

tutorial introduces a multi-pronged approach to address the challenges in meeting both the throughput and the energy efficiency goals for DNN training. It will incorporate a number of key features including the ability to support large-scale distributed DNN training tasks running on specialized (ASIC) hardware. Dataflow accelerators that support reduced precision computations and maintain high accelerator utilizations look promising as the industry looks to specialize beyond GPUs for Deep Learning.

Tutorial 3 Basics of Jitter in Wireline Communications

13:30-15:00 Ali Sheikholeslami University of Toronto, Canada

Biography Ali Sheikholeslami has been a professor at the University of Toronto, Canada, since 1999. His research interests are jitter, analog and digital integrated circuits, high-speed signaling, and memory design. He has published over 70 journal and conference articles including several on jitter. He has served as the ISSCC Education Chair since 2013, and as a member of its wireline committee from 2007 to 2013. Since 2016, he has been the Education Chair and the Distinguished Lecturer Program Chair for the Solid-State Circuits Society and an elected member of its Administration Committee. Prof. Sheikholeslami has received numerous teaching awards from the Faculty of Applied Science and Engineering at the University of Toronto. He is a co-author of a book entitled Understanding Jitter and Phase Noise, to appear in print by early 2018.

Abstract Jitter refers to deviation from ideal timing in clock and data transitions. In wireline communications, jitter reduces the timing margin available for clock and data recovery (CDR) circuits and poses significant challenges to signal integrity as the data rates march towards 64Gb/s/lane and beyond.

In this tutorial, we first review the basic definitions of jitter and its properties, the relationship between jitter and phase noise, and the effects of jitter on CDR and other building blocks of a wireline system. We then describe the concept of jitter transfer, jitter generation, and jitter tolerance curves, and the methods of characterizing, modeling, and simulating jitter. Finally, we present some recent works on jitter measurement and jitter mitigation techniques that are used to optimize the link performance

Tutorial 4 Emerging memory technology for IoT and AI applications

15:15-16:45 Takayuki Kawahara

- **Biography** Takayuki Kawahara is currently a Professor in the Department of Electrical Engineering at Tokyo University of Science, Katsushika, Japan. Sustainable electronics is the focus of his laboratory, which includes spin-current applications such as SOT-RAM. In the field of DRAM, his major contributions were low-voltage subthreshold-current reduction circuits. He also developed the world's first fully functional 2-Mb STT-RAM chip in 2007 and developed FD-SOI SRAM circuitry with back-gate control. From 1997 to 1998, he was a visiting researcher at the Swiss Federal Institute of Technology in Lausanne (EPFL). Prof. Kawahara is a recipient of the 9th (2009) Yamazaki-Teiichi Prize, the 2017 MEXT Commendation for Science and Technology, and he is an IEEE Fellow.
- Abstract We are enlightened through the progress of memory technology. It brings new materials and principles into the LSI field more frequently than any other technology. Moreover, commercial opportunities with considerable financial potential are possible. Artificial intelligence (AI) and the Internet of Things (IoT) have been attracting attention. In this lecture, first, emerging memory devices such as phase-change RAM (PCRAM), magnetoresistive random-access memory (MRAM), resistive random-access memory (RRAM), and the status of large-scale integration are summarized. Typical spin-transfer torque (STT), spin-orbit torque (SOT), and voltage-controlled writing technologies are described in detail, especially with regard to MRAM. Next, prospective memories using examples for AI and IoT applications are shown in a

Tokyo University of Science, Katsushika, Japan

cloud/server area and in a things/edge area. The development trends of AI and IoT are also surveyed. Design challenges to make use of non-volatility are emphasized in each application. Finally, a new movement in which memory devices evolve from wearable to implantable is discussed.



Prof. WEI has won many awards during last years, including the National 2nd Prize for Advanced Technology in 2002; the National 2nd Prize for Technology Invention in 2015; Beijing 1st and 2nd Prize for Advanced Technology in 2001 and 2004; the Award for Outstanding Chinese Patented Invention, State Intellectual Property Office of China & World Intellectual Property Organization in 2004 and 2015; the Outstanding Founder in Zhongguancun Science Park in 2001 and the Outstanding Leading Person in Semiconductor Industry, CSIA in 2003, etc.

With the fast growing of its economy, China has become the largest IC market in the world since Abstract 2013. The huge number of IC imported each year makes both suppliers and buyers be fear. From the suppliers' point of view, if China stopped to purchase IC that would be a catastrophe and from the buyers' side, if the suppliers stopped to sell IC to China, that would lead to a disaster. That is the background for China to announce its national plan to promote its native IC industry. Inevitably, this raised many questions. For example, what is the real state of the China's IC industry today, what implications does such a promotion have to the global IC, EDA and other related industries, and what goals are China's IC industry working to achieve? Obviously, with its rapid growth, China's IC industry is becoming an emerging force globally, increasing the importance of understanding the answers to these questions. Unfortunately, few people really understand China's IC industry. This presentation will give an overview of the Chinese IC market, followed by an introduction of China's IC industry. China's native products, design technologies, and talents will be described in detail to provide an objective and comprehensive picture of China's IC industry. As China is a unique country with huge population, vast territory, rapidly growing but unbalanced economy, and many diverse cultures, life-styles and traditions, its native product demands are also diverse. How to meet these drastically different requirements with a reasonable time to market while keeping costs low presents a big challenge. A rapidly growing IC industry in China will force engineers, both inside and outside China, to explore, to innovate as well as to collaborate. With a large talent pool addressing unique challenges, who can say there will not be new technologies, methodologies and products emerging to change the rules of the global information technology landscape?

2017 IEEE Asian Solid-State Circuits Conference (A-SSCC)



Session 2:	A1L-A Low-Power Programmable SoCs and Embedded Memories
Chair 1: Surhud K Chair 2: Daeyong	hare, Intel Corporation Shim, SK Hynix Convention Hall D (Convention Center 4F)
S2-1 (2027)	A Programmable RFSoC in 16nm FinFET Technology for Wideband Communications
10:45-11:10	Roberto Pelliconi, Daire Breathnach, Peng Lim, Ali Boumaalif, Patrick Lynch, Conrado Mesadri, David Melinn, Kwee Peng Yap, and Liam Madden <i>Xilinx Ireland, Dublin, Ireland</i>
S2-2 (2166)	A Reconfigurable Analog Baseband Transformer for Multistandard Applications in 14nm FinFET CMOS
11110 11100	Jongmi Lee, Jongwoo Lee, Chilun Lo, Jaehoon Lee, In-Young Lee, Byungki Han, Seunghyun Oh, and Thomas Cho
	Samsung Electronics, Korea
S2-3 (2136)	A 1.4Mb 40-nm embedded ReRAM macro with 0.07um ² bit cell, 2.7mA/100MHz low-
11:35-12:00	power read and hybrid write verify for high endurance application Chia-Fu Lee, Hon-Jarn Lin, Chiu-Wang Lien, Yu-Der Chih, and Jonathan Chang Taiwan Samicanductor Manufacturing Company, Taiwan
	Talwan semiconductor Manajactaring company, Talwan
S2-4 (2045)	A Dynamic Power Reduction in Synchronous 2RW 8T Dual-Port SRAM by Adjusting
12:00-12:25	Wordline Pulse Timing with Same/Different Row Access Mode
	Renesas Electronics Corporation, Tokyo, Japan
S2-5 (2067)	14nm Broadwell Xeon [®] Processor family: Design methodologies and optimizations
12:25-12:50	Mahesh K Kumashikar, Shridhar G Bendi, Srikanth Nimmagadda, Anup J Deka, and Anil Agarwal Intel Corporation, Bangalore, India

Session 3: A1L-D Circuits and Systems for Sensing and Security

Chair 1: Chung-Chih Hung, National Chiao Tung University *Chair 2:* Jun Deguchi, Toshiba Corp

Convention Hall E (Convention Center 4F)

S3-1 (2107)A Dual-Axis MEMS Vibratory Gyroscope ASIC with 0.0061°/s/vHz Noise Floor over 48010:45-11:10Hz Bandwidth
Zhichao Tan, Khiem Nguyen, Jeff Yan, Howard Samuels, Shane Keating, Paul Crocker, and Bill Clark

Zhichao Tan, Khiem Nguyen, Jeff Yan, Howard Samuels, Shane Keating, Paul Crocker, and Bill Clark Analog Devices, Inc., USA

S3-2 (2141)	Chaos, Deterministic Non-Periodic Flow, for Chip-Package-Board Interactive PUF
11:10-11:35	Noriyuki Miura, Masanori Takahashi, Kazuki Nagatomo, and Makoto Nagata
	Kobe University, Japan

S3-3 (2089) A 93μW 11Mbps Wireless Vital Signs Monitoring SoC with 3-Lead ECG, Bio-Impedance, and Body Temperature

Yuxuan Luo¹, Kok-Hin Teng¹, Yongfu Li¹, Wei Mao¹, Yong Lian², and Chun-Huat Heng¹ ¹National University of Singapore, Singapore ²York University, Canada

S3-4 (2090)A 16-Channel TDM Analog Front-end with Enhanced System CMRR for Wearable Dry12:00-12:25EEG Recording

Tao Tang^{1,2}, Wang Ling Goh¹, Lei Yao², and Yuan Gao² ¹Nanyang Technological University, Singapore, ²A*STAR, Singapore

S3-5 (2169)An Area-Efficient Amplifier-Less Digitally-Controlled Li-Ion Battery Charger in 0.35-μm12:25-12:50CMOS

Sheng-Ying Lin and Tsung-Hsien Lin National Taiwan University, Taiwan

Session 4: A2L-A Sensor Interface

Chair 1: Hao Yu, Nanyang Technological University *Chair 2:* Tetsuya Hirose, Kobe University

Convention Hall D (Convention Center 4F)

- S4-1 (2123)A 0.5V BJT-Based CMOS Thermal Sensor in 10-nm FinFET Technology13:50-14:15Da Shin Lin¹ and Hao Ping Hong²¹MediaTek, Taiwan,
²MediaTek USA, USA
- S4-2 (2138)An Ultra-low Power 169-nA 32.768-kHz Fractional-N PLL14:15-14:40Chun-Yu Lin, Tun-Ju Wang, Tzu-Hsuan Liu, and Tsung-Hsien Lin
National Taiwan University, Taiwan
- S4-3 (2062)A 10kHz-BW 93.7dB-SNR Chopped ΔΣ ADC with 30V Input CM Range and 115dB CMRR14:40-15:05at 10kHz
Long Xu, Johan H. Huijsing, and Kofi A.A. Makinwa

Delft University of Technology, The Netherlands

S4-4 (2143)An Energy-Efficient Self-Charged Crystal Oscillator with a Quadrature-Phase Shifter15:05-15:17Technique
Wei-Sung Chang, Dai-En Jhou, Yu-Hong Yang, and Tai-Cheng Lee

Wei-Sung Chang, Dai-En Jhou, Yu-Hong Yang, and Tai-Cheng Le National Taiwan University, Taiwan

S4-5 (2209) An Area-Efficient Capacitively-Coupled Sensor Readout Circuit with Current-Splitting

15:17-15:29 **OTA and FIR-DAC**

Chih-Chan Tu¹, Feng-Wen Lee^{1,2}, Han-Chun Chen¹, Yu-Kai Wang^{1,2} and Tsung-Hsien Lin¹ ¹National Taiwan University, Taiwan ²Mediatek, Taiwan

Session 5: A2L-B Digital Building Blocks

Chair 1: Keiichi Kushida, Toshiba Corporation *Chair 2:* Robert Chen-Hao Chang, National Chung Hsing University

Convention Hall B (Convention Center 4F)

S5-1 (2049)25 fJ/bit, 5Mb/s, 0.3V True Random Number Generator With Capacitively-Coupled13:50-14:15Chaos System and Dual-Edge Sampling Scheme
Anh Tuan Do and Xin Liu
Institute of Microelectronics, Agency for Science, Technology and Research (A*STAR), Singapore

S5-2 (2142)A 1.25pJ/bit 0.048mm² AES Core with DPA Resistance for IoT Devices14:15-14:40Shengshuo Lu¹, Zhengya Zhang¹, and Marios Papaefthymiou¹.²

¹University of Michigan, USA

²University of California, USA

- **S5-3 (2218)** A 0.40 pJ/cycle 981 μm² Voltage Scalable Digital Frequency Generator for SoC Clocking 14:40-15:05 Martin Cochet^{1,2}, Sylvain Clerc², Guénolé Lallement^{1,2}, Fady Abouzeid², Philippe Roche², and Jean-Luc Autran¹ ¹Aix-Marseille University & CNRS, France ²STMicroelectronics, France
- S5-4 (2188)A 10-GHz Multi-purpose Reconfigurable Built-in Self-Test Circuit for High-Speed Links15:05-15:30Myungguk Lee, Seungho Han, Jae-Yoon Sim, Hong-June Park, and Byungsub Kim
Pohang University of Science and Technology, Korea

Session 6: A2L-C PAM-4 Receiver Techniques

Chair 1: Wei-Zen Chen, National Chiao Tung University *Chair 2:* Hayun Chung, Korea University

Convention Hall C (Convention Center 4F)

S6-1 (2103)A 56Gbps PAM-4 Optical Receiver Front-end13:50-14:15Kuan-Lin Fu, and Shen-Iuan Liu
National Taiwan University, Taiwan

S6-2 (2129)	A Low-Power PAM4 Receiver Using 1/4-Rate Sampling Decoder with Adaptive Variable-
14:15-14:40	Gain Rectification
	Guang Zhu ¹ Quan Pan ² John Zhuang ³ Charlie Zhi ³ and C Patrick Yue ¹

Guang Zhu , Quan Pan , John Zhuang', Charlie Zhi', and C. Patrick Yue ¹The Hong Kong University of Science and Technology, Hong Kong ²Etopus, USA ³Brite Semiconductor, China

S6-3 (2050)A 82 mW 28 Gb/s PAM-4 Digital Sequence Decoder with built-in Error correction in14:40-15:0528nm FDSOI

Masum Hossain¹, Aurangozeb¹, AKM Delwar Hossain¹, and Maruf Mohammad²

¹University of Alberta, Canada ²Qualcomm Atheros, USA

S6-4 (2226)	A 51Gb/s, 320mW, PAM4 CDR with Baud-Rate Sampling for High-Speed Optical
15:05-15:30	Interconnects Nan Qi ^{1,2} , Yuhang Kang ³ , Qipeng Lin ³ , Jianxu Ma ⁴ , Jingbo Shi ² , Bozhi Yin ² , Chang Liu ² , Rui Bai ⁴ , Shang Hu ² , Juncheng Wang ² , Jiangbing Du ⁵ , Lin Ma ⁵ , Zuyuan He ⁵ , Ming Liu ³ , Feng Zhang ³ , and Patrick Yin Chiang ^{2,6} ¹ Institute of Semiconductors, Chinese Academy of Sciences, Beijing, China ² Fudan University, China ³ Institute of Microelectronics, Chinese Academy of Sciences, Beijing, China ⁴ PhotonIC Technologies, China ⁵ Shanghai Jiao Tong University, China ⁶ Oregon State University, USA
Session 7:	A2L-D Building Blocks for Frequency Synthesizers
<i>Chair 1:</i> Davide G <i>Chair 2:</i> Minoru F	uermandi, IMEC ujishima, Hiroshima University Convention Hall E (Convention Center 4F)
S7-1 (2052)	A 15-µW, 103-fs step, 5-bit Capacitor-DAC-based Constant-Slope Digital-to-Time
13:50-14:15	Converter in 28nm CMOS Peng Chen ¹ , Feifei Zhang ¹ , Zhirui Zong ² , Hao Zheng ¹ , Teerachot Siriburanon ¹ , and Robert Bogdan Staszewski ¹

¹University College Dublin, Ireland ²Delft University of Technology, the Netherlands

S7-2 (2047) 14:15-14:40	A 173–200 GHz Quadrature Voltage-Controlled Oscillator in 130 nm SiGe BiCMOS Paul Stärke, Vincent Rieß, Corrado Carta, and Frank Ellinger Technischen Universtität Dresden, Germany
S7-3 (2025) 14:40-15:05	A 67 GHz Dual Injection Quadrature VCO with -182.9 dBc/Hz FOM in 90-nm CMOS Cuei-Ling Hsieh, Hong-Shen Chen, Hou-Ru Pan, and Jenny Yi-Chun Liu National Tsing Hua University, Taiwan
S7-4 (2174)	A 350-mV 2.4-GHz Quadrature Oscillator with Nearly Instantaneous Start-Up Using
15:05-15:17	Series LC Tanks Yue Chen ¹ , Masoud Babaie ¹ , and Robert Bogdan Staszewski ^{1,2}

¹Delft University of Technology, The Netherlands ²University College Dublin, Ireland

S7-5 (2046) On-Chip Spur and Phase Noise Cancellation Techniques

15:17-15:29 Yi-An Li¹, Monte Mar², Borivoje Nikolić¹, and Ali M. Niknejad¹ ¹Berkeley Wireless Research Center (BWRC), University of California, USA ²The Boeing Company, USA

Convention Hall A (Convention Center 4F)

Session 8	Panel Discussion	
Organizer: Junghwan Choi, Samsung		

16:00-17:40 Future of Memory System and Technology

ModeratorKen Takeuchi, Chuo UniversityPanelists1.Introduction : Ken Takeuchi (Chuo

1.Introduction : Ken Takeuchi (Chuo University)
 2.3D Stack : (Package) Tae Je Cho (Samsung Electro-Mechanics)
 3.Circuits : (HBM) Daeyong Shim (SK Hynix)
 4.Systems : (PIM) Meng-Fan Chang (National Tsing Hua University)
 5.Applications : (AI and Big Data) Kihong Kim (SAP Korea VP)

A-SS DEZ Han Suldan	CC Plenary Speech
	November 8 (WED)
Sessio	n 9 Plenary Speech
	Convention Hall A (Convention Center 4F)
Plenary 3	Robots, IoT, and AI for Smarter Manufacturing Dr. Shinsuke Sakakihara
08.30-03.13	Executive Director & Chief Technical Advisor,
	Robot Business Division, Fanuc Corporation, Japan
Biography	Dr. Shinsuke Sakakibara, received BE from Applied Physics Department, the University of Tokyo, in 1972, and joined FANUC. He has been serving as a manager of research and development group of intelligent robot at FANUC since 1985 and initiating the research and development of intelligent robot with vision and force sensors for assembly use. He received his doctoral degree in engineering from the University of Tokyo in 1995.
	He has been serving as Honorary General Manager of Robot Laboratory at FANUC since 1999. He was appointed to President of RSJ, the Robotics Society of Japan, from 2009 to 2010. He was appointed to President of IFR, International Federation of Robotics, from 2012 to 2013. He has been serving as Executive Officer of FANUC since 2013. He has been serving as Executive Director & Chief Technical Advisor of FANUC since 2016.
Abstract	Robots are key for factory automation, such like Smart Manufacturing, and Industry 4.0. This Plenary talk covers introduction of the latest robot technologies and how they are being used for factory automation. The Plenary talk will cover "Collaborative Robots, " which are attracting much attention in recent years for their ability to collaborate with humans, allowing both robots and humans to focus on the abilities that they excel at. Also, the Plenary Talk introduces examples of the use of the IoT and AI in factories that has been automated through the introduction of robots and outline recent trends involving an open platform that facilitates such applications.
Plenary 4	Riding the Wave from Digital Consumer to Ubiquitous Intelligent Devices: Trends and
09:15-10:00	Opportunities of IC Design Dr. Kou-Hung Lawrence Loh Corporate Senior Vice President, MediaTek Inc. President, MediaTek USA Inc, USA
Biography	Dr. Kou-Hung Lawrence Loh is a Corporate Senior Vice President of MediaTek Inc. He oversees the company's Central Engineering Group, responsible for engineering the company's SOCs and chipsets design, development and implementation activities for all MediaTek's product lines including mobile communication, application processors, wireless connectivity, IOT, automotive, home entertainment, optical storage and broadband/networking business. He is also serving as President of MediaTek USA, Inc., responsible for the company's global operations in Europe and America.

Dr. Loh started his first circuit design position at IMP and later he joined Cirrus Logic, where his last position was Director of Analog IC Engineering. In 1998, he founded Silicon Bridge Inc., where he successfully led a number of analog/mixed-signal IC development projects with major semiconductor companies including MediaTek and Altera Corporation. Before joining MediaTek in 2004, he contributed to IC design industry in areas of read/write channels for magnetic and optical storage, high-performance analog filters, solid-state fingerprint sensors, highspeed SERDES and wireline transceivers for various business applications. He received his Ph.D. degree in Electrical Engineering from Texas A&M University, College Station, Texas. He has authored/co-authored dozens of technical papers/patents in areas of analog and mixed-signal integrated circuits/systems design and has contributed many panel talks and invited keynote speeches at numerous international conferences and professional communities. He served on ISSCC International Technical Program Committee for 5 consecutive years since 2005. He is currently serving on Steering Committee of A-SSCC and also on Board of Directors for Global Semiconductor Alliance (GSA).

Abstract For the past decade, mobile consumer devices have predominantly driven CMOS technologies to continue to follow the path of Moore's Law. Today we are ready to enter the era of "Intelligent Device" which creates even more business opportunities for semiconductor companies. End products may contain essential sensory or control components such as for medical, automotive or other internet of things (IoT) applications. The resulting massive data flows have created strong demands of local 'intelligence' which requires end devices to perform respective computing and connecting functions at the lowest possible energy levels. In this plenary talk, technology trends of IC designs to bring up modern and future intelligent devices are presented from a SOC company's perspective. Innovations in development of underlying technologies including systems, algorithms, circuits, packaging and fabricating process technologies, become increasingly challenging yet essential to ride the wave into ubiquitous intelligent devices.



Session 11: B1L-B Advanced Imaging System

2017 IEEE Asian Solid-State Circuits Conference (A-SSCC)

Chair 1: Youngcheol Chae, Yonsei University *Chair 2:* Jerald Yoo, National University of Singapore

Convention Hall B (Convention Center 4F)

S11-1 (2043)A CMOS Time of Flight (TOF) Depth Image Sensor with In-Pixel Background Cancellation10:30-10:55and Sensitivity Improvement Using Phase Shifting Readout TechniqueTing Liao, Nien-An Lee, and Chih-Cheng Hsieh

National Tsing Hua University, Taiwan

S11-2 (2110) An Element-Matched Band-Pass Delta-Sigma ADC for Ultrasound Imaging 10:55-11:20 Michele D'Urbino^{1,3}, Chao Chen¹, Zhao Chen¹, Zu-Yao Chang¹, Jacco Ponte², Boris Lippe², and Michiel Pertijs¹ ¹Delft University of Technology, The Netherlands ²Oldelft Ultrasound, The Netherlands ³Caeleste CVBA, Belgium

S11-3 (2190)A 12.1mW, 60dB SNR, 8-Channel Beamforming Embedded SAR ADC for Ultrasound11:20-11:45Imaging Systems

Taehoon Kim and Suhwan Kim Seoul National University, Korea

S11-4 (2207) A 2.79-mW 0.5%-THD CMOS Current Driver IC for Portable Electrical Impedance 11:45-12:10 Tomography System

Jaeeun Jang¹, Minseo Kim¹, Joonsung Bae², and Hoi-Jun Yoo¹ ¹Korea Advanced Institute of Science and Technology (KAIST), Korea ²Kangwon National University, Korea

S11-5 (2186)0.5 and 1.5 THz Monolithic Imagers in a 65 nm CMOS Adopting a VCO-Based Signal12:10-12:35Processing

Suna Kim, Kyoung-Yong Choi, Dae-Woong Park, Joo-Myoung Kim, Seok-Kyun Han, and Sang-Gug Lee

Korea Advanced Institute of Science and Technology (KAIST), Korea

Session 12: B1L-C Memory System

Chair 1: Kazutaka Miyano, Micron *Chair 2:* Ik Joon Chang, Kyunghee University

Convention Hall C (Convention Center 4F)

S12-1 (2009)Dual-Loop 2-step ZQ Calibration for Dedicated Power Supply Voltage in LPDDR4 SDRAM10:30-10:55Chang-Kyo Lee, Junha Lee, Ki-Ho Kim, Jin-Seok Heo, Gil-Hoon Cha, Jin-Hyeok Baek, Dae-Sik Moon,
Yoon-Joo Eom, Tae-Sung Kim, Hyunyoon Cho, Younghoon Son, Seonghwan Kim, Jong-Wook Park,
Sewon Eom, Si-Hyeong Cho, Young-Ryeol Choi, Seungseob Lee, Kyoung-Soo Ha, Youngseok Kim,
Bo-Tak Lim, Dae-Hee Jung, Eungsung Seo, Kyoung-Ho Kim, Yoon-Gyu Song, Youn-Sik Park, Tae-
Young Oh, Seung-Jun Bae, In-Dal Song, Seok-Hun Hyun, Joon-Young Park, Hyuck-Joon Kwon,Young-
Soo Sohn, Jung-Hwan Choi, Kwang-Il Park, and Seong-Jin Jang
Samsung Electronics, Korea

S12-2 (2224)MLC/3LC NAND Flash SSD Cache with Asymmetric Error Reduction Huffman Coding10:55-11:20for Tiered Hierarchical StorageHikaru Watanabe, Yoshiaki Deguchi, and Ken Takeuchi

Chuo University, Japan

S12-3 (2175) 11:20-11:45	Word-line Batch V _{TH} Modulation of TLC NAND Flash Memories for Both Write-Hot and Cold Data Yoshiaki Deguchi and Ken Takeuchi Chuo University, Japan
S12-4 (2065)	A 16kb Column-based Split Cell-VSS, Data-Aware Write-Assisted 9T Ultra-Low Voltage
11:45-12:10	SRAM with Enhanced Read Sensing Margin in 28nm FDSOI
	M. Sultan M. Siddiqui, Zhao Chuan Lee, and Tony Tae-Hyoung Kim Nanyang Technological University, Singapore
S12-5 (2204)	An Energy-optimized (37840, 34320) Symmetric BC-BCH Decoder for Healthy Mobile
12:10-12:22	Storages Seokha Hwang ¹ , Jaehwan Jung ² , Daesung Kim ³ , Jeongseok Ha ² , In-Cheol Park ² , and Youngjoo Lee ⁴ ¹ <i>Kwangwoon University, Korea</i> ² <i>Korea Advanced Institute of Science and Technology (KAIST), Korea</i> ³ <i>SK Hynix, Korea</i> ⁴ <i>Pohang University of Science and Technology (POSTECH), Korea</i>
S12-6 (2178)	A 130nm 1Mb HfO _x Embedded RRAM Macro Using Self-Adaptive Peripheral Circuit
12:22-12:34	System Techniques for 1.6X Work Temperature Range Feng Zhang ¹ , Dongyu Fan ^{1,2} , Yuan Duan ¹ , Jin Li ¹ , Cong Fang ¹ , Yun Li ¹ , Xiaowei Han ³ , Lan Dai ² , Chengying Chen ¹ , Jinshun Bi ¹ , Ming Liu ¹ , and Meng-Fan Chang ⁴ ¹ Institute of Microelectronics Chinese Academy of Sciences, China ² North China University of Technology, China ³ Xi'an UniIC Semiconductors Co., Ltd., China ⁴ National Tsing Hua University, Taiwan

Session 13: B1L-D Wireless Receivers and Transmitters

Chair 1: Tae Wook Kim, Yonsei University Chair 2: Chien-Nan Kuo, National Chiao Tung University

Convention Hall E (Convention Center 4F)

S13-1 (2076)A Reconfigurable Dual-Band WiFi/BT Combo Transceiver with Integrated 2G/BT SP3T,10:30-10:55LNA/PA Achieving Concurrent Receiving and Wide Dynamic Range Transmitting in
40nm CMOS

Meng-Hsiung Hung, Yi-Shing Shih, Chin-Fu Li, Wei-Kai Hong, Ming-Yeh Hsu, Chih-Hao Chen, Yu-Lun Chen, Chun-Wei Lin, and Yuan-Hung Chung *MediaTek Inc, Taiwan*

S13-2 (2195)A High-Speed DDFS MMIC with Frequency, Phase and Amplitude Modulations in 65nm10:55-11:20CMOS

Abdel Martinez Alonso, Masaya Miyahara, and Akira Matsuzawa Tokyo Institute of Technology, Japan

S13-3 (2160)A -121dBm Sensitivity, 2.8µJ/bit Rx, 8.8µJ/bit Tx, Narrowband transceiver for ARIB STD11:20-11:45and IoT

M. Kumarasamy Raja, Zhao Bin, Yan Dan Lei, Zhang Hongbao, Lim Wei Yi, and Chemmanda John Leo

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A*STAR (Agency for Science, Technology and Research), Singapore

S13-4 (2121)Detection of 3.0 THz wave with a detector in 65 nm standard CMOS process11:45-12:10Tong Fang, Zhao-yang Liu, Li-yuan Liu, Yuan-yuan Li, Jun-qi Liu, Jian Liu, and Nan-jian Wu
University of Chinese Academy of Sciences, China

S13-5 (2217)A 0.6-V 200-kbps 429-MHz Ultra-low-power FSK Transceiver in 90-nm CMOS12:10-12:35Chun-Yuan Chiu, Zhen-Cheng Zhang, and Tsung-Hsien Lin
National Taiwan University, Taiwan

Session 14: B2L-A Energy-efficient & Variation resilient Digital Circuits

Chair 1: Mototsugu Hamada, Keio University Chair 2: Yoonmyung Lee, Sungkyunkwan University

Convention Hall D (Convention Center 4F)

S14-1 (2028) An 82% Energy-Saving Change-Sensing Flip-Flop in 40nm CMOS for Ultra-Low Power 13:40-14:05 Applications Van Loi Le^{1,2}, Juhui Li², Alan Chang², and Tony T. Kim¹ ¹Nanyang Technological University, Singapore ²NXP Semiconductors, Singapore

- S14-2 (2150)NBTI/PBTI separated BTI monitor with 4.2x Sensitivity by Standard Cell Based14:05-14:30Unbalanced Ring OscillatorMitsuhiko Igarashi, Yoshio Takazawa, Yasumasa Tsukamoto, Kan Takeuchi, and Koji ShibutaniRenesas Electronics Corporation, Japan
- S14-3 (2034)A 0.44V-1.1V 9-Transistor Transition-Detector and Half-Path Error Detection Technique14:30-14:55for Low Power Applications
Xinchao Shang, Weiwei Shan, Longxing Shi, Xing Wan, and Jun Yang

Xinchao Shang, Weiwei Shan, Longxing Shi, Xing Wan, and Jun Yang Southeast University, China

S14-4 (2155)HTD: A Light-Weight Holosymmetrical Transition Detector Based In-situ Timing14:55-15:20Monitoring Technique for Wide-Voltage-Range in 40nm CMOSWentao Dai, Weiwei Shan, Xinning Liu, and Jun Yang
Southeast University, China

Session 15: B2L-B Nyquist-rate ADCs

Chair 1: Seung-Tak Ryu, KAIST Chair 2: Yan Zhu, University of Macau

Convention Hall B (Convention Center 4F)

- S15-1 (2133)A 0.5V 12-bitSAR ADC using Adaptive Time-Domain Comparator with Noise13:40-14:05Optimization
Chen-Che Kao, Sung-En Hsieh, and Chih-Cheng Hsieh
National Tsing Hua University, Taiwan
- **S15-2 (2203)**Range Pre-selection Sampling technique to reduce input drive energy for SAR ADCs14:05-14:30Harijot Singh Bindra¹, Joeri Lechevallier¹, Anne-Johan Annema¹, Simon Louwsma², Ed van Tuijl^{1,2},

and Bram Nauta¹ ¹University of Twente, The Netherlands ²Teledyne DALSA, The Netherlands

S15-3 (2064) A 5-bit 2 GS/s Binary-Search ADC with Charge-Steering Comparators

14:30-14:55 U-Fat Chio, Sai-Weng Sin¹, Seng-Pan U^{1,2}, Franco Maloberti³, and R. P. Martins^{1,4}
¹University of Macau, Macao, China
²Synopsys Macau Ltd., Macao, China
³University of Pavia, Italy
⁴Instituto Superior Técnico/Universidade de Lisboa, Portugal

S15-4 (2083)A 13-bit 160MS/s Pipelined Subranging-SAR ADC with Low-Offset Dynamic Comparator14:55-15:07Weitao Li, Fule Li, Jia Liu, Hongyu Li, and Zhihua Wang
Tsinghua University, China

S15-5 (2114) A 1.5fJ/Conv-step 10b 100kS/s SAR ADC with Gain-Boosted Dynamic Comparator 15:07-15:19 Xiyuan Tang, Long Chen, Jeonggoo Song, and Nan Sun

L5:19 Xiyuan Tang, Long Chen, Jeonggoo Song, and Nan Sun The University of Texas at Austin, USA

Session 16: B2L-C Machine Learning and Recognition SoCs

Chair 1: Byeong-Gyu Nam, Chungnam National University *Chair 2:* Tsung-Te Liu, National Taiwan University

Convention Hall C (Convention Center 4F)

S16-1 (2137) A 2.56mm² 718GOPS Configurable Spiking Convolutional Sparse Coding Processor in 13:40-14:05 40nm CMOS

Chester Liu, Sung-Gun Cho, and Zhengya Zhang University of Michigan, USA

S16-2 (2206)A 21mW Low-power Recurrent Neural Network Accelerator with Quantization Tables14:05-14:30for Embedded Deep Learning Applications
Jinmook Lee, Dongjoo Shin, and Hoi-Jun Yoo

Korea Advanced Institute of Science and Technology (KAIST), Korea

S16-3 (2015)EQSCALE: Energy-Quality Scalable Feature Extraction Engine for Sub-mW Real-time14:30-14:55Video Processing with 0.55 mm2 Area in 40nm CMOS

Anastacia B. Alvarez², Gopalakrishnan Ponnusamy¹, and Massimo Alioto¹ ¹National University of Singapore, Singapore ²University of the Philippines, Philippines

S16-4 (2227)A Self-Powered Always-On Vision-based Wake-up Detector for Wearable Gesture User14:55-15:20Interfaces

Suhwan Cho, Seongrim Choi, Junsik Woo, Ara Kim, and Byeong-Gyu Nam Chungnam National University, Korea

Session 17: B2L-D Advanced Wireline Clock Generators and Transmitters

Chair 1: Jung-Hoon Chun, Sungkyunkwan University

Convention Hall E (Convention Center 4F)

2017 IEEE Asian Solid-State Circuits Conference (A-SSCC)

Chair 2: Ziqiang Wang, Tsinghua University

S17-1 (2094) 13:40-14:05	A 18-to-23 GHz -253.5dB-FoM Sub-Harmonically Injection-Locked ADPLL with ILFD Aided Adaptive Injection Timing Alignment Technique Zhao Zhang, Jincheng Yang, Liyuan Liu, Peng Feng, Jian Liu, and Nanjian Wu University of Chinese Academy of Sciences, China
S17-2 (2115)	A 1.5-GHz Sub-Sampling Fractional-N PLL for Spread-Spectrum Clock Generator in 0.18-
14:05-14:30	μm CMOS
	Chun-Yu Lin, Tun-Ju Wang, and Tsung-Hsien Lin
	National Taiwan University, Taiwan
S17-3 (2191)	A 2.1Gbps 12-Channel Transmitter with Phase Emphasis Embedded Serializer for UHD
14:30-14:55	Intra-panel Interface
	Jihwan Park, Joo-Hyung Chae, Yong-Un Jeong, Jae-Whan Lee, and Suhwan Kim
	Seoul National University, Korea
S17-4 (2099)	A Low-Power Dual-Mode 20-Gb/s NRZ and 28-Gb/s PAM-4 Voltage-Mode Transmitter
14:55-15:20	Hae-Woong Yang ¹ , Ashkan Roshan-Zamir ¹ , Young-Hoon Song ² , and Samuel Palermo ¹
	¹ Texas A&M University, USA
	² NXP Semiconductor, USA

Session 18: B3L-A Analog Techniques

Chair 1: Po-Hung Chen, National Chiao Tung University *Chair 2:* Hyun-Sik Kim, Dankook University

Convention Hall D (Convention Center 4F)

S18-1 (2117)	Subthreshold Voltage Reference With Nwell/Psub Diode Leakage Compensation for
15:50-16:15	Low-Power High-Temperature Systems
	Inhee Lee, Dennis Sylvester, and David Blaauw
	University of Michigan, USA
S18-2 (2192)	A Smart-Offset Analog LDO with 0.3V Minimum Input Voltage and 99.1% Current
16:15-16:40	Efficiency
	Saurabh Chaubey and Ramesh Harjani
	University of Minnesota, USA
S18-3 (2151)	A 762-µW 16.3-ps Resolution Digital Pulse Width Modulator Using Zooming Phase-
16:40-17:05	Interpolator
	Masanobu Tsuji
	ROHM Co., Ltd., Japan
S18-4 (2157)	Fully-Integrated AMLED Micro Display System With a Hybrid Voltage Regulator
17:05-17:17	Junmin Jiang, Liusheng Sun, Xu Zhang, Shing Hin Yuen, Xianbo Li, Wing-Hung Ki, C. Patrick Yue, and
	Kei May Lau
	The Hong Kong University of Science and Technology, Hong Kong
S18-5 (2197)	A Low-Voltage Low-Offset Dual Strong-Arm Latch Comparator
17:17-17:29	Aikaterini Papadopoulou ¹ , Vladimir Milovanović ² , and Borivoje Nikolić ¹

¹University of California at Berkeley, USA ²University of Kragujevac, Serbia

Session 19: B3L-B High-resolution ADCs

Chair 1: Liyuan Liu, Chinese Academy of Sciences *Chair 2:* Jintae Kim, Konkuk University, Korea

Convention Hall B (Convention Center 4F)

S19-1 (2032)	A 5.35 mW 10 MHz Bandwidth CT Third-Order $\Delta\Sigma$ Modulator with Single Opamp
15:50-16:15	Achieving 79.6/84.5 dB SNDR/DR in 65 nm CMOS
	Wei Wang ¹ , Yan Zhu ¹ , Chi-Hang Chan ¹ , Seng-Pan U ^{1,2} , and Rui Paulo Martins ^{1,3}
	¹ University of Macau, Macao, China
	² Synopsys Macau Ltd., Macao, China
	³ Instituto Superior Técnico/Universidade de Lisboa, Portugal
S19-2 (2120)	A 72.9-dB SNDR 20-MHz BW 2-2 Discrete-Time Sturdy MASH Delta-Sigma Modulator
16:15-16:40	Using Source-Follower-Based Integrators
	Yong-Sik Kwak, Kang-Il Cho, Ho-Jin Kim, Seung-Hoon Lee, and Gil-Cho Ahn
	Sogang University, Korea
S19-3 (2042)	A Compact 87.1-dB DR Bandwidth-Scalable Delta-Sigma Modulator Based on Dynamic
16:40-17:05	Gain-Bandwidth-Boosting Inverter for Audio Applications
	Young-Ha Hwang, Jun-Eun Park, and Deog-Kyoon Jeong
	Seoul National University, Korea
S19-4 (2176)	A 172dB-FoM Pipelined SAR ADC Using a Regenerative Amplifier with Self-Timed Gain
17:05-17:30	Control and Mixed-Signal Background Calibration
	Miguel Gandara ¹ , Paridhi Gulati ² , and Nan Sun ¹
	¹ The University of Texas at Austin, USA
	² Analog Devices, Inc., USA

Session 20: B3L-C IPs for Emerging Applications

Chair 1: Chun Zhang, Tsinghua UniversityConvention Hall C (Convention Center 4F)Chair 2: Pei-Yun Tsai, National Central UniversityConvention Hall C (Convention Center 4F)

S20-1 (2016)A Fully-SynthesizableC-ElementBasedPUFFeaturingTemperatureVariation15:50-16:15Compensation with Native 2.8% BER, 1.02fJ/b at 0.8-1.0V in 40nm
Sachin Taneja, Anastacia Alvarez, Gopalakrishnan Sadagopan, and Massimo Alioto

National University of Singapore, Singapore

S20-2 (2202)	A 0.37mm ² LTE/Wi-Fi Compatible, Memory-Based, Runtime-Reconfigurable 2 ⁿ 3 ^m 5 ^k FFT
16:15-16:40	Accelerator Integrated with a RISC-V Core in 16nm FinFET
	Angie Wang, Brian Richards, Palmer Dabbelt, Howard Mao, Stevo Bailey, Jaeduk Han, Eric Chang,
	James Dunn, Elad Alon, and Borivoje Nikolić
	University of California, USA

S20-3 (2200)	A 65nm 376nA 0.4V Linear Classifier Using Time-Based Matrix-Multiplying ADC with
16:40-17:05	Non-Linearity Aware Training
	Anvesha A and Arijit Raychowdhury
	Georgia Institute of Technology, USA
S20-4 (2167)	A 1GHz Fault Tolerant Processor with Dynamic Lockstep and Self-recovering Cache for
17:05-17:30	ADAS SoC Complying with ISO26262 in Automotive Electronics
	Jinho Han ^{1,2} , Youngsu Kwon ¹ , Yong Cheol Peter Cho ¹ , and Hoi-Jun Yoo ²
	¹ Electronics and Telecommunications Research Institute(ETRI), Korea
	-Korea Advanced Institute of Science and Technology(KAIST), Korea
Session 21	B3L-D High performance RF Frequency generation Techniques
Chair 1: Miniae L	ee. Gwangiu Institute of Science and Technology
Chair 2: Taizo Yan	nawaki, Hitachi Convention Hall E (Convention Center 4F)
S21-1 (2194)	A 77-GHz Mixed-Mode FMCW Signal Generator Based on Bang-Bang Phase Detector
15:50-16:15	Jianfu Lin ¹ , Zheng Song ¹ , Nan Qi ² , Woogeun Rhee ¹ , and Baoyong Chi ¹
	² Tsinghua University, China ² Chinasa Anadema of Salamana, China
	Chinese Academy of Sciences, China
S21-2 (2125)	A 7GHz-Bandwidth 31.5 GHz FMCW-PLL with Novel Twin-VCOs Structure in 65nm CMOS
16:15-16:40	Shunli Ma,Jili Sheng, Ning Li, and Junyan Ren
	Fudan University, China
S21-3 (2071)	A -245 dB FOM 48 fs rms jitter semi-digital PLL with intrinsic temperature compensation
16:40-17:05	in 130 nm CMOS
	J. Anders ¹ , S. Bader ¹ , M. Dietl ² , P. Sareen ² , G. Rombach ² , S. Tambouris ² , and M. Ortmanns ¹
	¹ University of Ulm, Germany
	Texas Instruments Germany, Germany
S21-4 (2080)	An Ultra-Low Phase Noise All-Digital Multi-Frequency Generator Using Injection-Locked
17:05-17:30	DCOs and Time-Interleaved Calibration
	Suneui Park, Heein Yoon, and Jaehyouk Choi
	Ulsan national Institute of Science and Technology(UNIST), Korea